IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Art Unit : 2812 Applicant : Johannes Baur et al.

Patent No.: 7,169,632 Examiner : Savitri Mulpuri Conf. No . 2117

Issue Date: January 30, 2007

Serial No.: 10/657.841 Filed : September 9, 2003

Title : RADIATION-EMITTING SEMICONDUCTOR COMPONENT AND METHOD

FOR PRODUCING THE SEMICONDUCTOR COMPONENT

MAILSTOP CERTIFICATE OF CORRECTIONS

Commissioner for Patents P.O. Box 1450

Alexandria, VA 22313-1450

TRANSMITTAL OF REQUEST FOR CERTIFICATE OF CORRECTION

Applicant hereby requests that a certificate of correction be issued for the abovereferenced patent in accordance with the attached request.

All errors sought to be corrected were made in printing by the U.S. Patent and Trademark Office, as evidenced by the attached initialed PTO Forms 1449, and no fee is believed to be due.

Please apply any other required fees to deposit account 06-1050, referencing the attorney docket number shown above

Respectfully submitted,

Ido Rabinovitch Reg. No. L0080

PTO Customer No. 26161 Fish & Richardson P.C. Telephone: (617) 542-5070 Facsimile: (617) 542-8906

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UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

Page 1 of 2

PATENT No. : 7,169,632

APPLICATION NO : 10/657.841

DATED : JANUARY 30, 2007

INVENTOR(S) : JOHANNES BAUR, DOMINIK EISERT, MICHAEL FEHRER, BERTHOLD HAHN, VOLKER

HÄRLE, MARIANNE ORTMANN, UWE STRAUSS, JOHANNES VÖLKL AND ÜLRICH

ZEHNOER

It is certified that an error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Page 2, column 1, line 8,

U.S. PATENT DOCUMENTS,

insert	6,291,839 B1	09/2001	Lester
	3,343,026	09/1967	Lucchinger et al.
	5,814,839	09/1998	Hosoba
	5,087,674	02/1992	Gardner et al.
	2003/0116791 A1	06/2003	Baptist et al.
	2003/0127654 A1	07/2003	Eisert et al.
	6,229,160 B1	05/2001	Krames et al

Page 2, column 2, line 7,

FOREIGN PATENT DOCUMENTS.

insert	DE	199 27 945 A1	03/2000
	DE	198 07 758 A1	12/1998
	DE	43 24 325 A1	01/1994
	DE	42 18 806 A1	12/1993
	DE	27 27 508 A1	01/1979

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Ido Rabinovitch Fish & Richardson P.C. P.O. Box 1022 Mioneapolis, Minnesota 55440-1022 Staple Here Only

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

Page 2 of 2

PATENT NO. : 7,169,632 APPLICATION NO : 10/657,841

APPEICATION 10/037,641

DATEO : JANUARY 30, 2007

INVENTOR(S) : JOHANNES BAUR, DOMINIK EISERT, MICHAEL FEHRER, BERTHOLD HAHN, VOLKER

HÄRLE, MARIANNE ORTMANN, UWE STRAUSS, JOHANNES VOLKL AND ÜLRICH

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ZEHNDER

It is certified that an error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

WO	01/93310 A2	12/2001
WO	01/61765 A1	08/2001
UK.	2 271 087 A	04/1994
EP	0 611 131 A1	08/1994
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EP	0 810 674 A2	12/1997
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Page 2, column 2, line 7,

OTHER PUBLICATIONS

insert -- J. Zhang et al. "Precise microfabrication of wide band gap semiconductors (SiC and GaN) by VUV-UV multiwavelength laser ablation", Applied Surface Science, Vol. 127-129, pp. 793-799, 1998.

W. N. Carr. "Photometric Figures of Merit for Semiconductor Luminescent Sources Operating in Spontaneous Mode", Infrared Physics, Vol. 6, pp. 1-19, 1966. —

Mailing Appress of Sender:

Ido Rabinovitch Fish & Richardson P.C. P.O. Box 1022 Minneapolis, Minnesota 55440-1022

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F	2003/0127654 A1	7/10/03	Eisert et al.				
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FORM PTO-1449 (SUBSTITUTE) US DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Attorney Docket No.: P2001,0176 Appl. No.: Applicant: JOHANNES BAUR ET AL.					
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Sheet 1 of 1 FORM PTO-1449 (SUBSTITUTE) Attorney Docket No : Applic, No. P2001.0176 10/657.841 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE Apolicant INFORMATION DISCLOSURE Johannes Baur et al. STATEMENT BY APPLICANT (37 CFR 1.98(b)) Filing Date Group Art Unit September 9, 2003 U.S. PATENT DOCUMENTS INITIALS PATENT NO. DATE PATENTEE CLASS CLASS DATE A 8 D ε ç G Н 3 FOREIGN PATENT DOCUMENT TRANSI DOCUMENT NO. DATE COUNTRY CLASS CLASS YESINO 61 110 476 05/28/86 Japan × × 8.6 M OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.) J. Zhang et al.; "Precise microfabrication of wide band gap semiconductors (SIC and GaN) by VUV-UV multiwavelength laser ablation", Applied Surface Science, Vol. 127-129, 1998, pp. 793-799

i U EXAMINER: Initial if cliation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

7-19

EXAMINER

W. N. Carr: "Photometric Figures Of Merit For Semiconductor Luminescent Sources Operating in Spontaneous Mode", Infrared Physics, 1968, Vol. 6, pp.

DATE CONSIDERED